IN THE SPECIFICATION

Please replace the paragraph at page 17, prenumbered lines 25-27, with the following rewritten paragraph:

Fig. 7 is a cross-sectional view illustrating a state that a mask has been arranged on one surface of the anisotropically conductive sheet <u>body</u>.

Please replace the paragraph at page 38, prenumbered lines 7-26, with the following rewritten paragraph:

A pair of, for example, electromagnets are then arranged on an upper surface of the ferromagnetic base plate 51 in the top force 50 and a lower surface of the ferromagnetic base plate 56 in the bottom force 55, and the electromagnets are operated, thereby applying a parallel magnetic field having an intensity distribution, i.e., a parallel magnetic field having higher intensity between the ferromagnetic substance portions layers 52 in the top force 50 and their corresponding ferromagnetic substance portions layers 57 in the bottom force 55, to the molding material layer 11A in the thickness-wise direction thereof. As a result, in the molding material layer 11A, as illustrated in Fig. 4, the conductive particles P dispersed in the molding material layer 11A are gathered at portions 12A to become the conductive parts, which are located between the ferromagnetic substance portions layers 52 in the top force 50 and their corresponding ferromagnetic substance portions layers 57 in the bottom force 55, and at the same time oriented so as to align in the thickness-wise direction of the molding material layer.

Please replace the paragraph at page 51, prenumbered line 20, to page 52, prenumbered line 24, with the following rewritten paragraph:

A pair of, for example, electromagnets are then arranged on an upper surface of the ferromagnetic base plate 51 in the top force 50 and a lower surface of the ferromagnetic base plate 56 in the bottom force 55, and the electromagnets are operated, whereby the conductive particles dispersed in the molding material layers [[20A]] 11A are gathered at portions to become the conductive parts 12, which are located between the ferromagnetic substance layers 52 of the top force 50 and their corresponding ferromagnetic substance layers 57 of the bottom force 55, and oriented so as to align in the thickness-wise direction of the molding material layers. In this state, the molding material layers [[20A]] 11A are subjected to a curing treatment, whereby a plurality of anisotropically conductive sheet bodies 11, in each of which a plurality of conductive parts 12 with the conductive particles contained in the elastic polymeric substance in a state oriented so as to align in the thickness-wise direction are arranged in a state mutually insulated by an insulating part 13 composed of the elastic polymeric substance, in which the conductive particles are not present at all or scarcely present, are formed in a state fixed to the respective opening edges of the frame plate 18, thereby producing an intermediate [[10A]] 20A for connector composed of the frame plate 18 having the plurality of the openings 19 corresponding to regions, in which electrodes to be inspected have been arranged, in all integrated circuits formed on a wafer, which is an object of inspection, and the plurality of the anisotropically conductive sheet bodies 11 arranged so as to close the respective openings 19 in this frame plate 18 and supported by the respective opening edges of the frame plate 18 as illustrated in Fig. 14.

Please replace the paragraph at page 52, prenumbered line 25, to page 53, prenumbered line 2, with the following rewritten paragraph:

Thereafter, a DLC film is formed on each of the surfaces of the anisotropically conductive sheet bodies 11 in the intermediate [[10A]] 20A for connector, thereby obtaining the anisotropically conductive connector 20 shown in Figs. 10 and 11.

Please replace the paragraph at page 53, prenumbered lines 3-8, with the following rewritten paragraph:

According to such an anisotropically conductive connector 20, since the connector has the anisotropically conductive sheets [[18]] 10, in which the DLC film 15 has been formed, the effects brought about by the above-described anisotropically conductive sheet sheets 10 are achieved, and moreover the following additional effects are brought about.

Please replace the paragraph at page 59, prenumbered line 23, to page 60, prenumbered line 5, with the following rewritten paragraph:

The circuit board 30 for inspection has the same construction as the circuit board 30 for inspection in the wafer inspection apparatus shown in Figs. 14 and 15 15 and 16, and the anisotropically conductive connector 20 has the same construction as the anisotropically conductive connector 20 in the wafer inspection apparatus shown in Figs. 14 and 15 15 and 16 except that the conductive parts 12 of the anisotropically conductive sheet body 11 in each of the anisotropically conductive sheets 10 thereof are formed in a state protruded from both surfaces of the insulating part 13.

Please replace the paragraph at page 73, prenumbered line 12, to page 74, prenumbered line 14, with the following rewritten paragraph:

As illustrated in Fig. 21, 596 square integrated circuits L in total, which each had dimensions of 6.5 mm x 6.5 mm, were formed on a wafer 1 made of silicon (coefficient of linear thermal expansion: 3.3×10^{-6} /K) and having a diameter of 8 inches. Each of the integrated circuits L formed on the wafer 1 has a region A of electrodes to be inspected at its center as illustrated in Fig. 22. In the region A of the electrodes to be inspected, as illustrated in Fig. 23, 26 electrodes 2 to be inspected each having dimensions of 200 μ m in a vertical direction (upper and lower direction in Fig. 23) and 60 μ m in a lateral direction (left and right direction in Fig. 23) are arranged at a pitch of 120 µm in 2 lines (the number of electrodes to be inspected in a line: 13) in the lateral direction. A clearance between electrodes [[7]] 2 to be inspected adjoining in the vertical direction is 250 μ m. Every two electrodes among the 26 electrodes 2 to be inspected are electrically connected to each other. The electrodes 2 to be inspected are each composed of a rectangular flat plate-like aluminum pad, and the total number of the electrodes 2 to be inspected in the whole of the wafer 1 is 15,496. This wafer will hereinafter be referred to as "Wafer W1 for Test". Sixty-four integrated circuits L (8 by 8 integrated circuits in vertical and lateral directions) arranged in vertical and lateral directions as indicated by a bold line in Fig. 24 were selected from among the 596 integrated circuits formed on Wafer 1 for Test, and a region, in which these 64 integrated circuits L had been formed, was regarded as "Test Region E1".

Please cancel the original Abstract at page 106, lines 1-20, in its entirety and insert therefor the following substitute Abstract on a separate sheet as follows: